

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   |              |  | Symbol           | Value      | Unit |
|--|--------------|--|------------------|------------|------|
| Drain-Source Voltage                                     |              |  | V <sub>DSS</sub> | 30         | V    |
| Gate-Source Voltage                                      |              |  | V <sub>GSS</sub> | ±25        | V    |
| Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V  | Steady State | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | I <sub>D</sub>   | 5.3<br>4.2 | A    |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V  | Steady State | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | I <sub>D</sub>   | 8.0<br>6.3 | A    |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V  | t ≤ 10s      | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | I <sub>D</sub>   | 9.5<br>7.7 | A    |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V | Steady State | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | I <sub>D</sub>   | 6.5<br>4.9 | A    |
| Continuous Drain Current (Note 6) V <sub>GS</sub> = 4.5V | t ≤ 10s      | T <sub>A</sub> = +25°C<br>T <sub>A</sub> = +70°C | I <sub>D</sub>   | 7.8<br>6.2 | A    |
| Pulsed Drain Current (Note 7)                            |              |  | I <sub>DM</sub>  | 70         | A    |
| Avalanche Current (Notes 7 & 8)                          |              |  | I <sub>AR</sub>  | 18         | A    |
| Repetitive Avalanche Energy (Notes 7 & 8) L = 0.1mH      |              |  | E <sub>AR</sub>  | 16         | mJ   |

**Thermal Characteristics**

| Characteristic   | Symbol                            | Max         | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 5)   | P <sub>D</sub>                    | 1.0         | W    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 5)         | R <sub>θJA</sub>                  | 130.6       | °C/W |
| Power Dissipation (Note 6)   | P <sub>D</sub>                    | 2.07        | W    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6)         | R <sub>θJA</sub>                  | 62.5        | °C/W |
| Power Dissipation (Note 6) t ≤ 10s   | P <sub>D</sub>                    | 3.0         | W    |
| Thermal Resistance, Junction to Ambient @T <sub>A</sub> = +25°C (Note 6) t ≤ 10s | R <sub>θJA</sub>                  | 43.8        | °C/W |
| Operating and Storage Temperature Range  | T <sub>J</sub> , T <sub>STG</sub> | -55 to +150 | °C   |

- Notes:
5. Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
  6. Device mounted on 2" x 2" FR-4 PCB with high coverage 2 oz. Copper, single sided.
  7. Repetitive rating, pulse width limited by junction temperature.
  8. I<sub>AR</sub> and E<sub>AR</sub> rating are based on low frequency and duty cycles to keep T<sub>J</sub> = +25°C.

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

| Characteristic   | Symbol              | Min | Typ  | Max  | Unit | Test Condition   |
|--|---------------------|-----|------|------|------|--|
| <b>OFF CHARACTERISTICS (Note 9)</b>                    |                     |     |      |      |      |  |
| Drain-Source Breakdown Voltage                         | BV <sub>DSS</sub>   | 30  | -    | -    | V    | V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA   |
| Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C | I <sub>DSS</sub>    | -   | -    | 0.1  | μA   | V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V  |
| Gate-Source Leakage                                    | I <sub>GSS</sub>    | -   | -    | ±100 | nA   | V <sub>GS</sub> = ±25V, V <sub>DS</sub> = 0V   |
| <b>ON CHARACTERISTICS (Note 9)</b>                     |                     |     |      |      |      |  |
| Gate Threshold Voltage                                 | V <sub>GS(th)</sub> | 0.8 | 1.2  | 2.0  | V    | V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250μA                                 |
| Static Drain-Source On-Resistance                      | R <sub>DS(on)</sub> | -   | 13.5 | 20   | mΩ   | V <sub>GS</sub> = 10V, I <sub>D</sub> = 10A  |
|  |                     | -   | 22   | 27   |      | V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 7.5A  |
| Forward Transfer Admittance                            | Y <sub>fs</sub>     | -   | 13.0 | -    | S    | V <sub>DS</sub> = 5V, I <sub>D</sub> = 10A   |
| Diode Forward Voltage                                  | V <sub>SD</sub>     | -   | 0.7  | 1.0  | V    | V <sub>GS</sub> = 0V, I <sub>S</sub> = 1A  |
| <b>DYNAMIC CHARACTERISTICS (Note 10)</b>               |                     |     |      |      |      |  |
| Input Capacitance                                      | C <sub>iss</sub>    | -   | 580  | -    | pF   | V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V,<br>f = 1.0MHz                                 |
| Output Capacitance                                     | C <sub>oss</sub>    | -   | 110  | -    |      |  |
| Reverse Transfer Capacitance                           | C <sub>rss</sub>    | -   | 70   | -    |      |  |
| Gate Resistance  | R <sub>g</sub>      | -   | 2.0  | 3.0  | Ω    | V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz                                       |
| Total Gate Charge V <sub>GS</sub> = 4.5V               | Q <sub>g</sub>      | -   | 5.3  | -    | nC   | V <sub>GS</sub> = 4.5V, V <sub>DS</sub> = 15V, I <sub>D</sub> = 10A                        |
| Total Gate Charge V <sub>GS</sub> = 10V                | Q <sub>g</sub>      | -   | 11.3 | -    |      |  |
| Gate-Source Charge                                     | Q <sub>gs</sub>     | -   | 1.9  | -    |      |  |
| Gate-Drain Charge                                      | Q <sub>gd</sub>     | -   | 1.9  | -    |      |  |
| Turn-On Delay Time                                     | t <sub>D(on)</sub>  | -   | 4.4  | -    | ns   | V <sub>GS</sub> = 10V, V <sub>DS</sub> = 15V,<br>R <sub>L</sub> = 15Ω, R <sub>G</sub> = 6Ω |
| Turn-On Rise Time                                      | t <sub>r</sub>      | -   | 4.6  | -    | ns   |  |
| Turn-Off Delay Time                                    | t <sub>D(off)</sub> | -   | 19.5 | -    | ns   |  |
| Turn-Off Fall Time                                     | t <sub>f</sub>      | -   | 5.8  | -    | ns   |  |
| Body Diode Reverse Recovery Time                       | t <sub>rr</sub>     | -   | 12.6 | -    | ns   | IF=8A, di/dt=500A/μs   |
| Body Diode Reverse Recovery Charge                     | Q <sub>rr</sub>     | -   | 10.5 | -    | nC   |  |

Notes: 9. Short duration pulse test used to minimize self-heating effect.  
10. Guaranteed by design. Not subject to production testing.

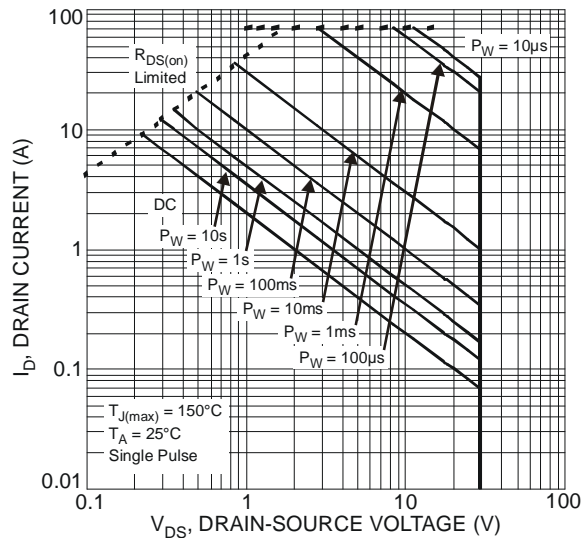


Fig. 1 SOA, Safe Operation Area

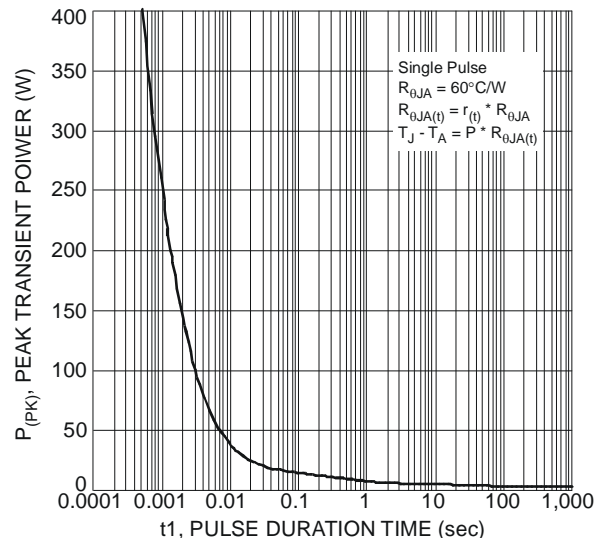
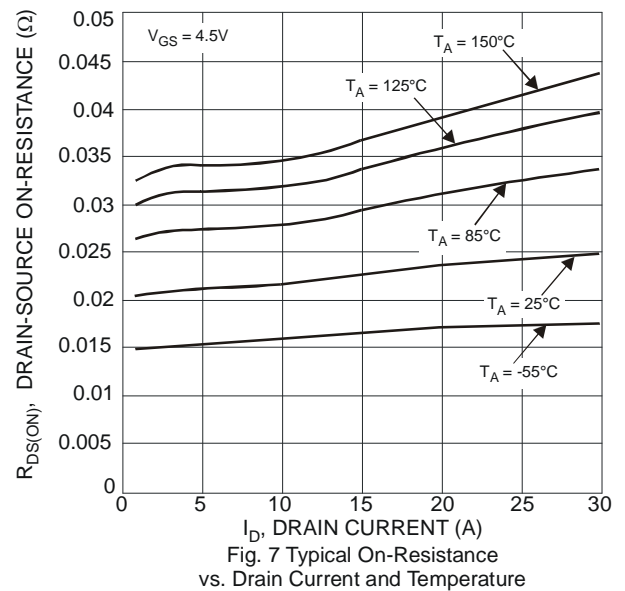
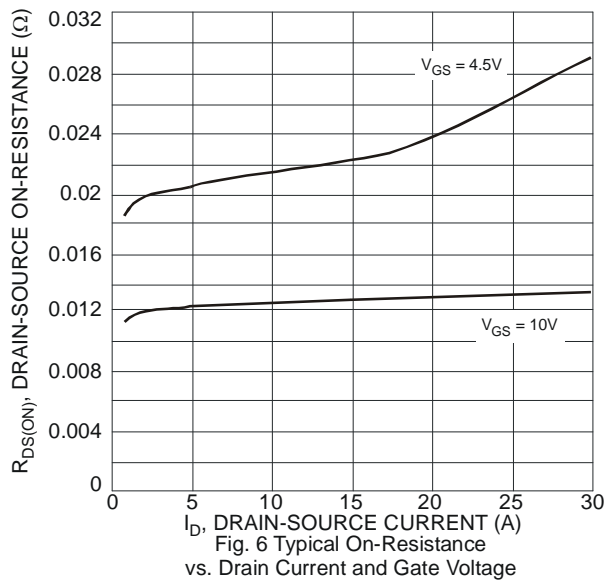
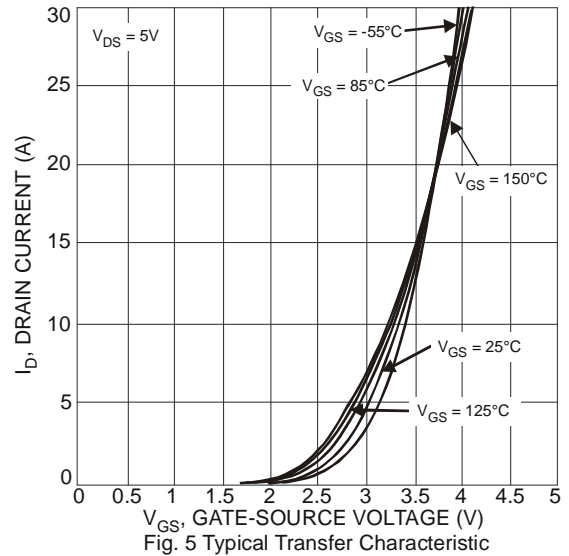
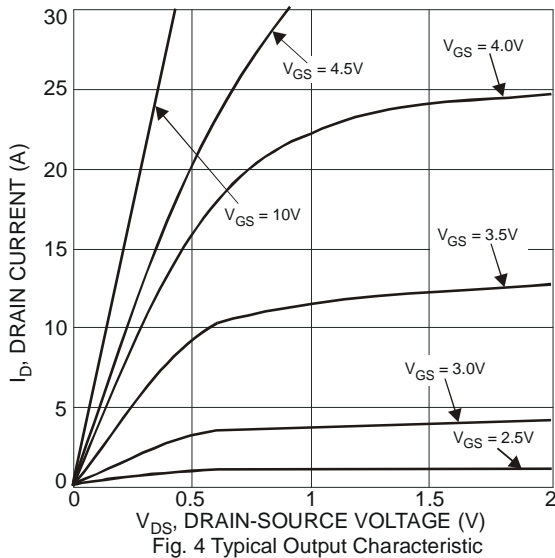
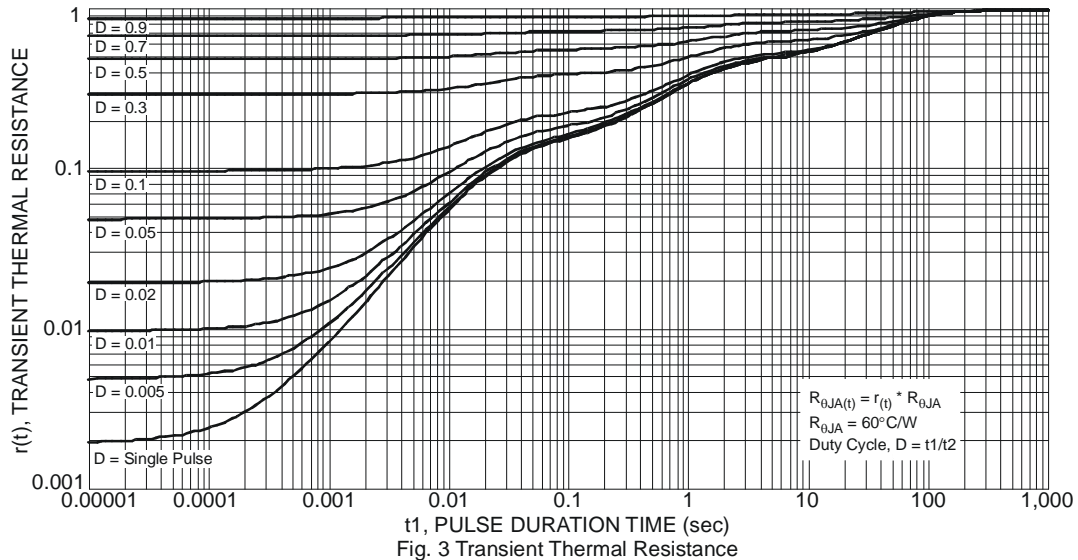


Fig. 2 Single Pulse Maximum Power Dissipation



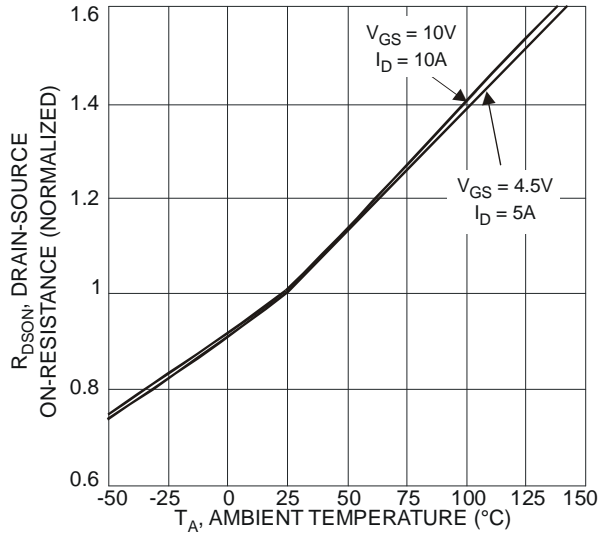


Fig. 8 On-Resistance Variation with Temperature

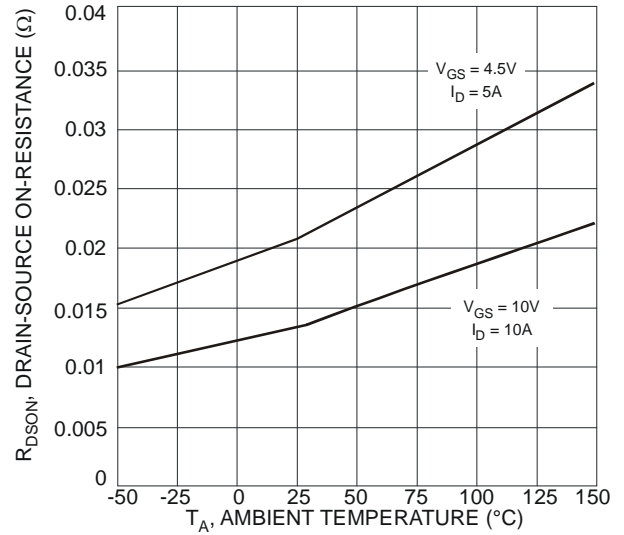


Fig. 9 On-Resistance Variation with Temperature

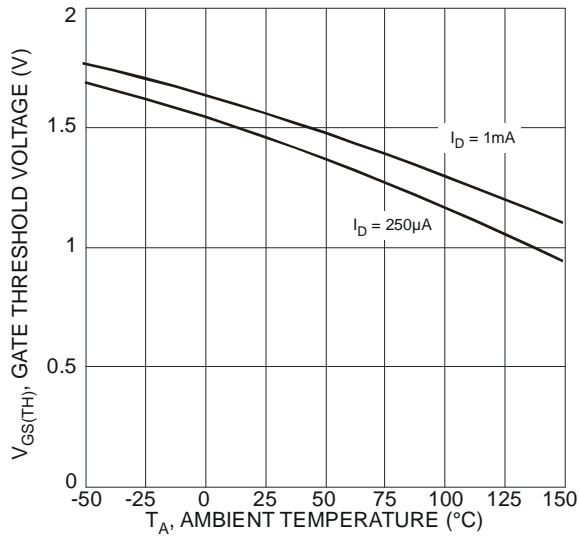


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

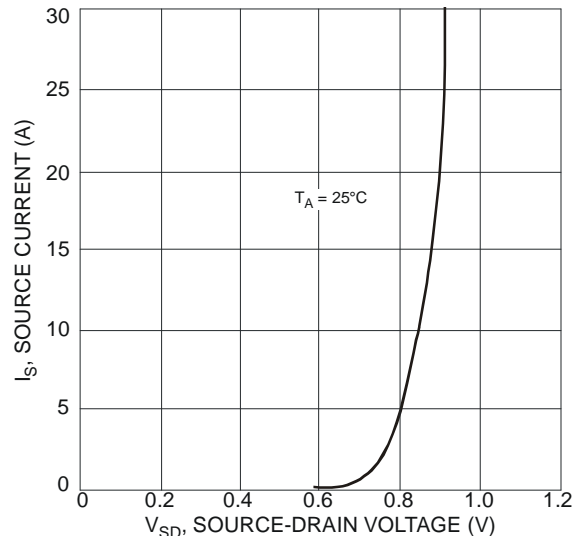


Fig. 11 Diode Forward Voltage vs. Current

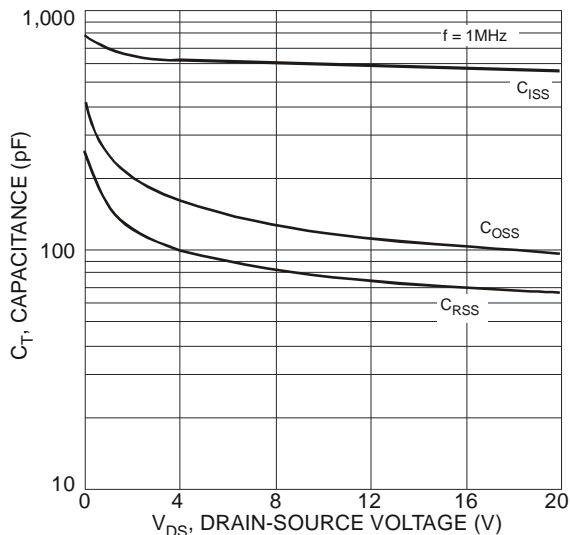


Fig. 12 Typical Total Capacitance

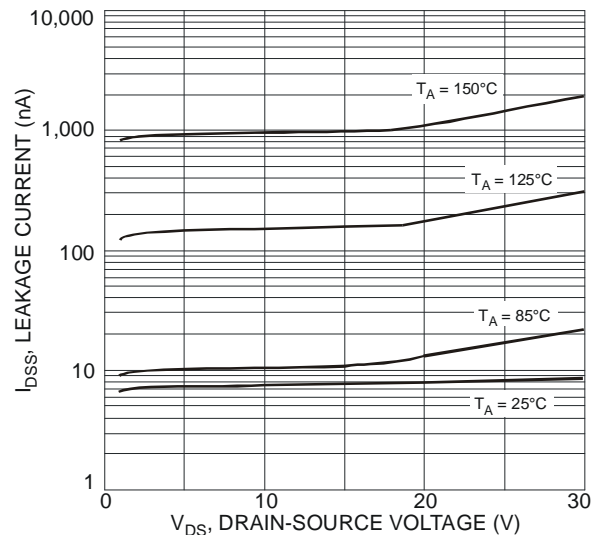
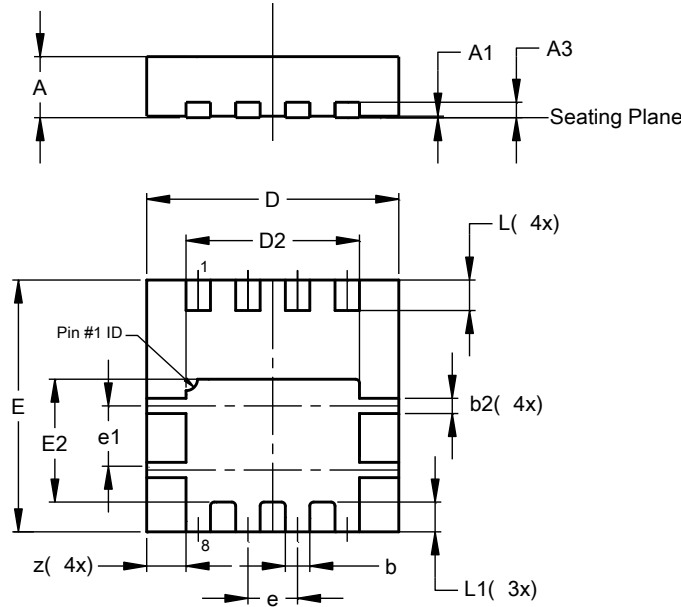


Fig. 13 Typical Leakage Current vs. Drain-Source Voltage

## Package Outline Dimensions

Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.

### POWERDI® 3333-8

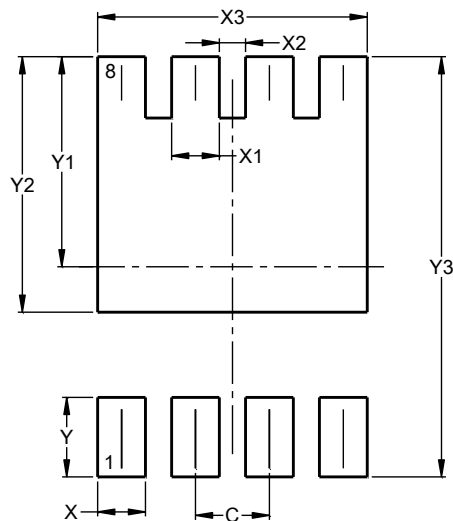


| POWERDI® 3333-8      |      |      |       |
|----------------------|------|------|-------|
| Dim                  | Min  | Max  | Typ   |
| A                    | 0.75 | 0.85 | 0.80  |
| A1                   | 0.00 | 0.05 | 0.02  |
| A3                   | —    | —    | 0.203 |
| b                    | 0.27 | 0.37 | 0.32  |
| b2                   | —    | —    | 0.20  |
| D                    | 3.25 | 3.35 | 3.30  |
| D2                   | 2.22 | 2.32 | 2.27  |
| E                    | 3.25 | 3.35 | 3.30  |
| E2                   | 1.56 | 1.66 | 1.61  |
| e                    | —    | —    | 0.65  |
| e1                   | 0.79 | 0.89 | 0.84  |
| L                    | 0.35 | 0.45 | 0.40  |
| L1                   | —    | —    | 0.39  |
| z                    | —    | —    | 0.515 |
| All Dimensions in mm |      |      |       |

## Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.

### POWERDI® 3333-8



| Dimensions | Value (in mm) |
|------------|---------------|
| C          | 0.650         |
| X          | 0.420         |
| X1         | 0.420         |
| X2         | 0.230         |
| X3         | 2.370         |
| Y          | 0.700         |
| Y1         | 1.850         |
| Y2         | 2.250         |
| Y3         | 3.700         |

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